



**COMPLEMENTARY SILICON POWER
DARLINGTON TRANSISTORS**

..designed for use as output devices in complementary general purpose amplifier applications.

FEATURES:

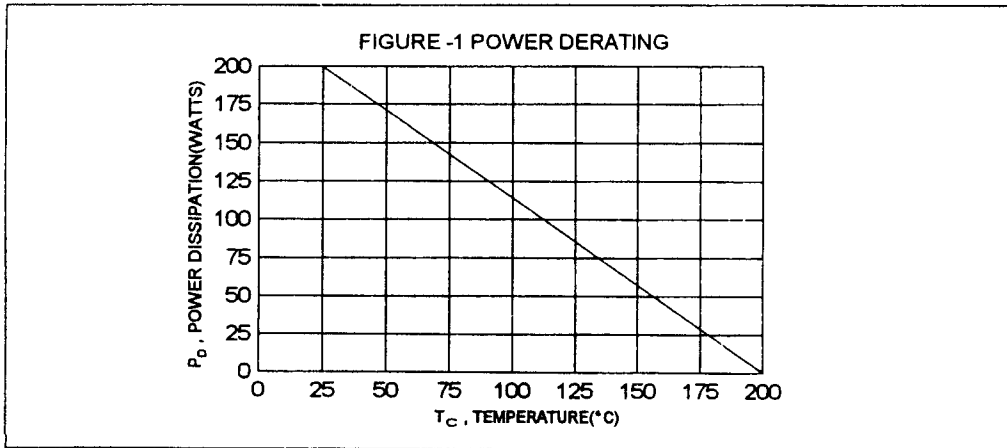
- * High Gain Darlington Performance
- * High DC Current Gain $h_{FE} = 1000(\text{Min}) @ I_C = 20 \text{ A}$
- * Monolithic Construction with Built-in Base-Emitter Shunt Resistor

MAXIMUM RATINGS

Characteristic	Symbol	MJ11011	MJ11013	MJ11015	Unit
		MJ11012	MJ11014	MJ11016	
Collector-Emitter Voltage	V_{CEO}	60	90	120	V
Collector-Base Voltage	V_{CBO}	60	90	120	V
Emitter-Base Voltage	V_{EBO}	5.0			V
Collector Current-Continuous -Peak	I_C	30			A
	I_{CM}	50			
Base Current	I_B	1.0			A
Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	200			W
		1.15			
Operating and Storage Junction Temperature Range	T_J, T_{STG}	- 65 to +200			$^\circ\text{C}$

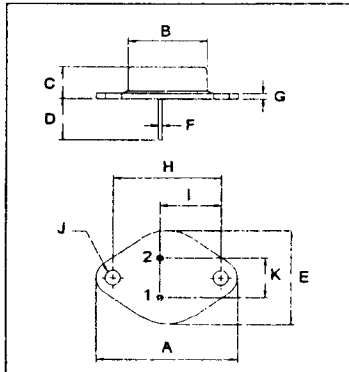
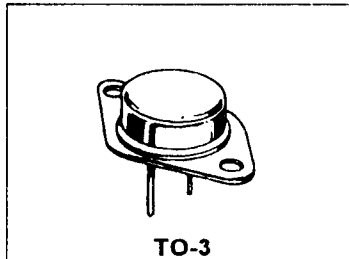
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance Junction to Case	$R_{\theta jc}$	0.87	$^\circ\text{C}/\text{W}$



PNP	NPN
MJ11011	MJ11012
MJ11013	MJ11014
MJ11015	MJ11016

30 AMPERE
COMPLEMENTARY
SILICON POWER
DARLINGTON TRANSISTOR
60-120 VOLTS
200 WATTS



PIN 1.BASE
2.EMITTER
COLLECTOR(CASE)

DIM	MILLIMETERS	
	MIN	MAX
A	38.75	39.96
B	19.28	22.23
C	7.96	9.28
D	11.18	12.19
E	25.20	26.67
F	0.92	1.09
G	1.38	1.62
H	29.90	30.40
I	16.64	17.30
J	3.88	4.36
K	10.67	11.18

MJ11011, MJ11013, MJ11015 PNP / MJ11012, MJ11014, MJ11016 NPN

ELECTRICAL CHARACTERISTICS ($T_c = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Collector - Emitter Sustaining Voltage (1) ($I_c = 100\text{ mA}$, $I_B = 0$) MJ11011, MJ11012 MJ11013, MJ11014 MJ11015, MJ11016	$V_{CE(sus)}$	60 90 120		V
Collector Cutoff Current ($V_{CE} = 50\text{ V}$, $I_B = 0.0$)	I_{CEO}		1.0	mA
Collector-Emitter Leakage Current ($V_{CE} = 60\text{ V}$, $R_{BE} = 1.0\text{ k ohm}$) MJ11011, MJ11012 ($V_{CE} = 90\text{ V}$, $R_{BE} = 1.0\text{ k ohm}$) MJ11013, MJ11014 ($V_{CE} = 120\text{ V}$, $R_{BE} = 1.0\text{ k ohm}$) MJ11015, MJ11016 ($V_{CE} = 60\text{ V}$, $R_{BE} = 1.0\text{ k ohm}$, $T_c = 125^\circ\text{C}$) MJ11011, MJ11012 ($V_{CE} = 90\text{ V}$, $R_{BE} = 1.0\text{ k ohm}$, $T_c = 125^\circ\text{C}$) MJ11013, MJ11014 ($V_{CE} = 120\text{ V}$, $R_{BE} = 1.0\text{ k ohm}$, $T_c = 125^\circ\text{C}$) MJ11015, MJ11016	I_{CER}		1.0 1.0 1.0 5.0 5.0 5.0	mA
Emitter Cutoff Current ($V_{EB} = 5.0\text{ V}$, $I_C = 0$)	I_{EBO}		5.0	mA

ON CHARACTERISTICS (1)

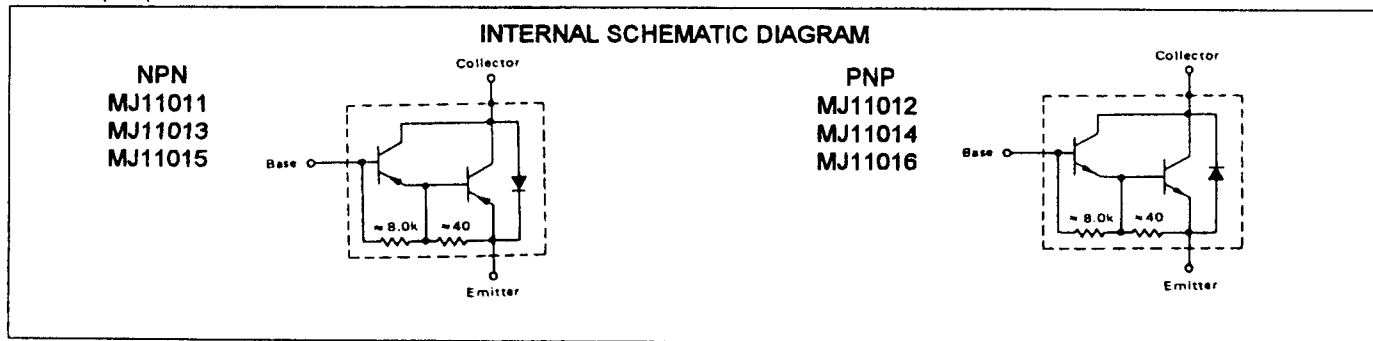
DC Current Gain ($I_c = 20\text{ A}$, $V_{CE} = 5.0\text{ V}$) ($I_c = 30\text{ A}$, $V_{CE} = 5.0\text{ V}$)	hFE	1000 200		
Collector-Emitter Saturation Voltage ($I_c = 20\text{ A}$, $I_B = 200\text{ mA}$) ($I_c = 30\text{ A}$, $I_B = 300\text{ mA}$)	$V_{CE(sat)}$		3.0 4.0	V
Base-Emitter Saturation Voltage ($I_c = 20\text{ A}$, $I_B = 200\text{ mA}$) ($I_c = 30\text{ A}$, $I_B = 300\text{ mA}$)	$V_{BE(sat)}$		3.5 5.0	V

DYNAMIC CHARACTERISTICS

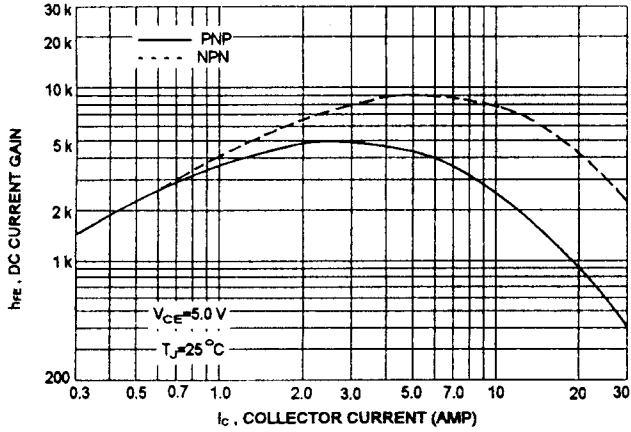
Small-Signal Current Gain ($I_c = 10\text{ A}$, $V_{CE} = 3.0\text{ V}$, $f = 1.0\text{ MHz}$)	$ h_{fe} $	4.0		
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(1) Pulse Test: Pulse width = 300 us , Duty Cycle $\leq 2.0\%$

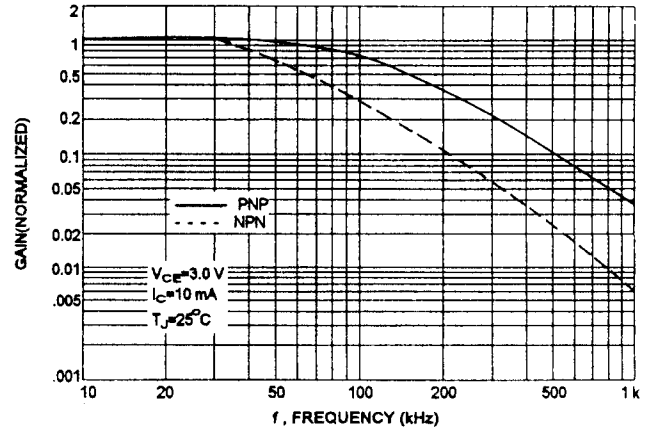
(2) $f_T = |h_{fe}| \cdot f_{test}$



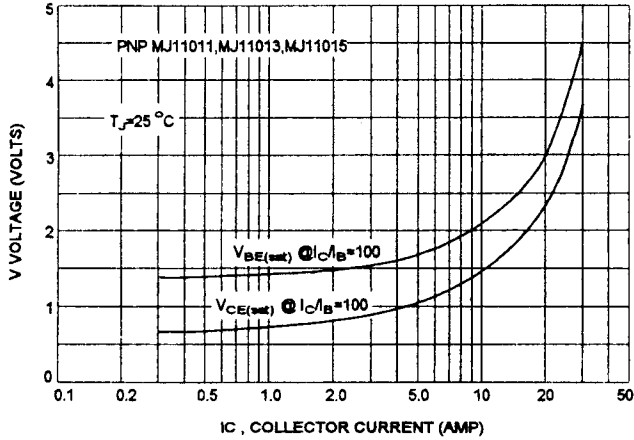
DC CURRENT GAIN



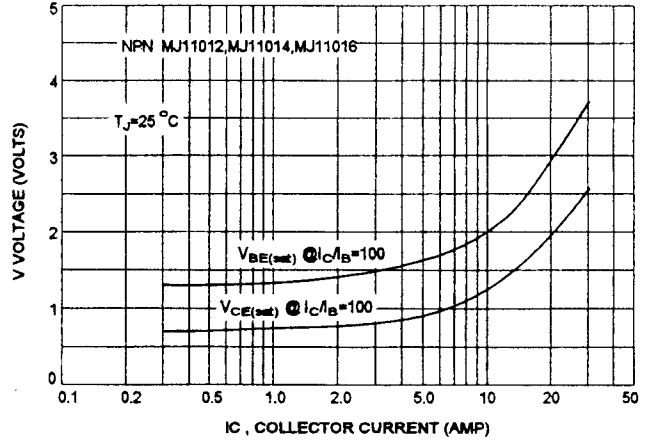
SMALL-SIGNAL CURRENT GAIN



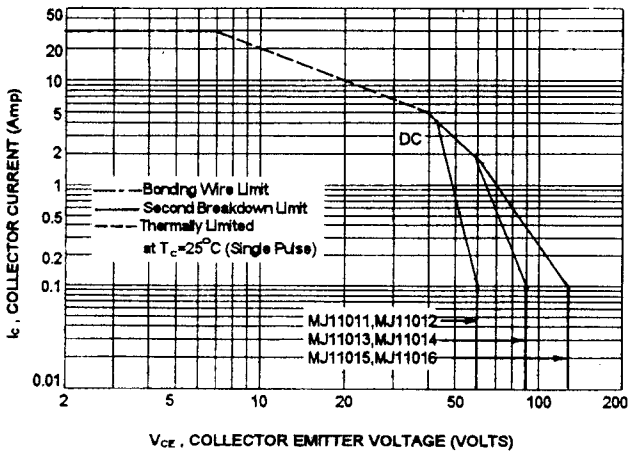
"ON" VOLTAGES



"ON" VOLTAGES



ACTIVE-REGION SAFE OPERATING AREA (SOA)



There are two limitation on the power handling ability of a transistor: average junction temperature and second breakdown safe operating area curves indicate I_C - V_{CE} limits of the transistor that must be observed for reliable operation i.e., the transistor must not be subjected to greater dissipation than curves indicate.

The data of SOA curve is base on $T_{J(PK)} = 200^\circ C$; T_C is variable depending on conditions. second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(PK)} \leq 200^\circ C$. At high case temperatures, thermal limitation will reduce the power that can be handled to values less than the limitations imposed by second breakdown.